

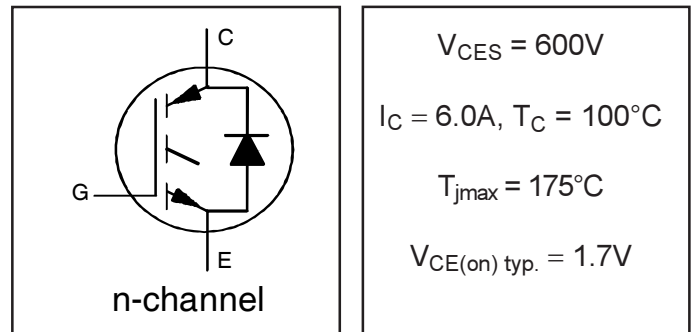
## INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

### Features

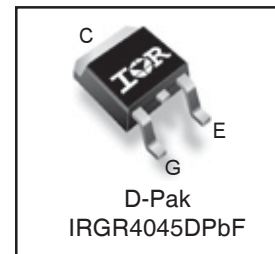
- Low  $V_{CE(on)}$  Trench IGBT Technology
- Low Switching Losses
- Maximum Junction temperature 175 °C
- 5µs SCSOA
- Square RBSOA
- 100% of the parts tested for  $I_{LM}$ ①
- Positive  $V_{CE(on)}$  Temperature Coefficient.
- Ultra Fast Soft Recovery Co-pak Diode
- Tighter Distribution of Parameters
- Lead-Free, RoHS Compliant

### Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low  $V_{CE(ON)}$  and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI



$V_{CES} = 600V$
$I_C = 6.0A, T_C = 100^\circ C$
$T_{jmax} = 175^\circ C$
$V_{CE(on) typ.} = 1.7V$



<b>G</b>	<b>C</b>	<b>E</b>
Gate	Collector	Emitter

### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	12	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.0	
$I_{CM}$	Pulsed Collector Current, $V_{GE} = 15V$	18	
$I_{LM}$	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	24	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	8.0	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	4.0	
$I_{FM}$	Diode Maximum Forward Current ②	24	
$V_{GE}$	Continuous Gate-to-Emitter Voltage	$\pm 20$	V
	Transient Gate-to-Emitter Voltage	$\pm 30$	
$P_D @ T_C = 25^\circ$	Maximum Power Dissipation	77	W
	$P_D @ T_C = 100^\circ$	Maximum Power Dissipation	
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	$^\circ C$
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT ③	---	---	1.9	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode ③	---	---	6.8	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑤	---	---	50	
$R_{\theta JA}$	Junction-to-Ambient	---	---	110	

\*Qualification standards can be found at <http://www.irf.com/>

### Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

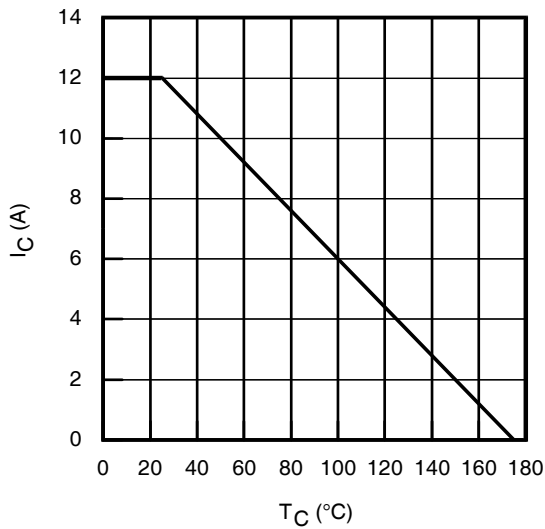
	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref. Fig
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 100\mu A$ ④	CT 6
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.36	—	V/°C	$V_{GE} = 0V, I_C = 250\mu A$ ( 25 - 175 °C ) ④	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 6.0A, V_{GE} = 15V, T_J = 25^\circ\text{C}$	5,6,7,9, 10,11
		—	2.07	—		$I_C = 6.0A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	
		—	2.14	—		$I_C = 6.0A, V_{GE} = 15V, T_J = 175^\circ\text{C}$	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	—	6.5	V	$V_{CE} = V_{GE}, I_C = 150\mu A$	9,10,11,12
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-13	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$ ( 25 - 175 °C )	
$g_{fe}$	Forward Transconductance	—	5.8	—	S	$V_{CE} = 25V, I_C = 6.0A, PW = 80\mu s$	
$I_{CES}$	Collector-to-Emitter Leakage Current	—	—	25	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$	8
		—	—	250		$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$	
$V_{FM}$	Diode Forward Voltage Drop	—	1.60	2.30	V	$I_F = 6.0A$	
		—	1.30	—		$I_F = 6.0A, T_J = 175^\circ\text{C}$	
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$	

### Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

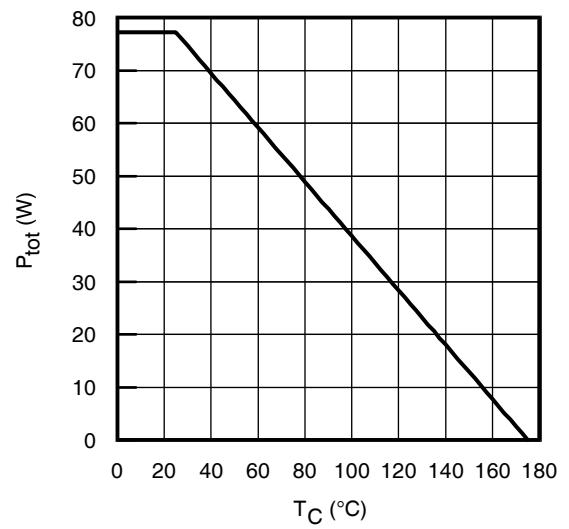
	Parameter	Min.	Typ.	Max. ⑥	Units	Conditions	Ref. Fig
$Q_g$	Total Gate Charge (turn-on)	—	13	19.5	nC	$I_C = 6.0A$	24
$Q_{ge}$	Gate-to-Emitter Charge (turn-on)	—	3.1	4.65		$V_{CC} = 400V$	CT 1
$Q_{gc}$	Gate-to-Collector Charge (turn-on)	—	6.4	9.6		$V_{GE} = 15V$	
$E_{on}$	Turn-On Switching Loss	—	56	86	$\mu J$	$I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V$	CT 4
$E_{off}$	Turn-Off Switching Loss	—	122	143		$R_G = 47\Omega, L = 1mH, L_S = 150nH, T_J = 25^\circ\text{C}$	
$E_{total}$	Total Switching Loss	—	178	229		Energy losses include tail and diode reverse recovery	
$t_{d(on)}$	Turn-On delay time	—	27	35	ns	$I_C = 6.0A, V_{CC} = 400V$	CT 4
$t_r$	Rise time	—	11	15		$R_G = 47\Omega, L = 1mH, L_S = 150nH$	
$t_{d(off)}$	Turn-Off delay time	—	75	93		$T_J = 25^\circ\text{C}$	
$t_f$	Fall time	—	17	22			
$E_{on}$	Turn-On Switching Loss	—	140	—	$\mu J$	$I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V$	13,15
$E_{off}$	Turn-Off Switching Loss	—	189	—		$R_G = 47\Omega, L = 1mH, L_S = 150nH, T_J = 175^\circ\text{C}$	CT 4
$E_{total}$	Total Switching Loss	—	329	—		Energy losses include tail and diode reverse recovery	WF 1, WF 2
$t_{d(on)}$	Turn-On delay time	—	26	—	ns	$I_C = 6.0A, V_{CC} = 400V$	14,16
$t_r$	Rise time	—	12	—		$R_G = 47\Omega, L = 1mH, L_S = 150nH$	CT 4
$t_{d(off)}$	Turn-Off delay time	—	95	—		$T_J = 175^\circ\text{C}$	WF 1, WF 2
$t_f$	Fall time	—	32	—			
$C_{ies}$	Input Capacitance	—	350	—	pF	$V_{GE} = 0V$	23
$C_{oes}$	Output Capacitance	—	29	—		$V_{CC} = 30V$	
$C_{res}$	Reverse Transfer Capacitance	—	10	—		$f = 1Mhz$	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 24A$ $V_{CC} = 500V, V_p = 600V$ $R_G = 100\Omega, V_{GE} = +20V \text{ to } 0V$	4 CT 2
SCSOA	Short Circuit Safe Operating Area	—	5	—	$\mu s$	$V_{CC} = 400V, V_p = 600V$ $R_G = 100\Omega, V_{GE} = +15V \text{ to } 0V$	22 CT 3, WF 4
$E_{rec}$	Reverse recovery energy of the diode	—	178	—	$\mu J$	$T_J = 175^\circ\text{C}$	17,18,19
$t_{rr}$	Diode Reverse recovery time	—	74	—	ns	$V_{CC} = 400V, I_F = 6.0A$	20,21
$I_{rr}$	Peak Reverse Recovery Current	—	12	—	A	$V_{GE} = 15V, R_G = 47\Omega, L = 1mH, L_S = 150nH$	WF 3

#### Notes:

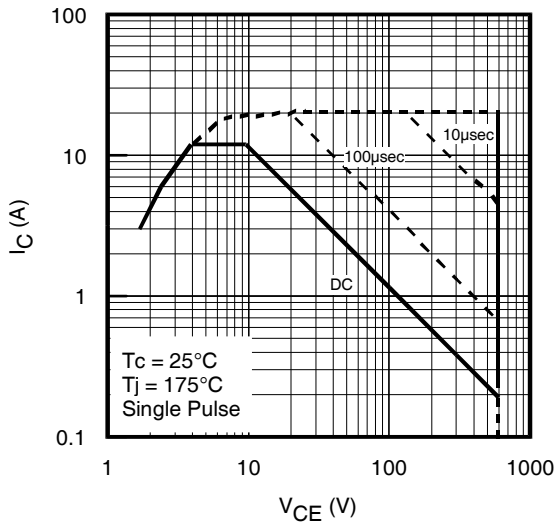
- ①  $V_{CC} = 80\% (V_{CES}), V_{GE} = 15V, L = 1.0mH, R_G = 47\Omega$ .
- ② Pulse width limited by max. junction temperature.
- ③  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .
- ④ Refer to AN-1086 for guidelines for measuring  $V_{(BR)CES}$  safely.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑥ Maximum limits are based on statistical sample size characterization.



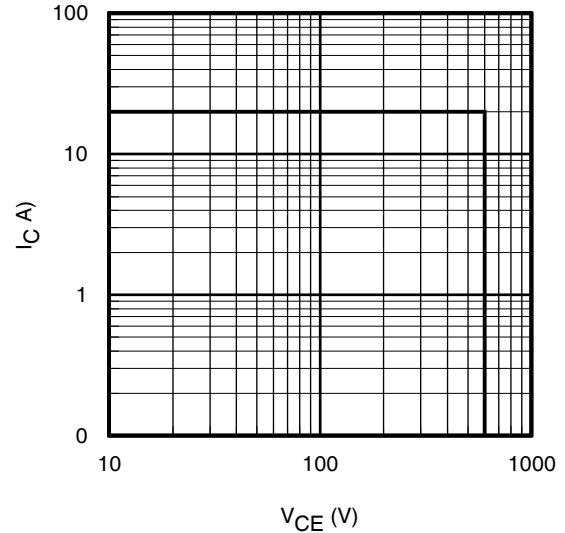
**Fig. 1** - Maximum DC Collector Current vs. Case Temperature



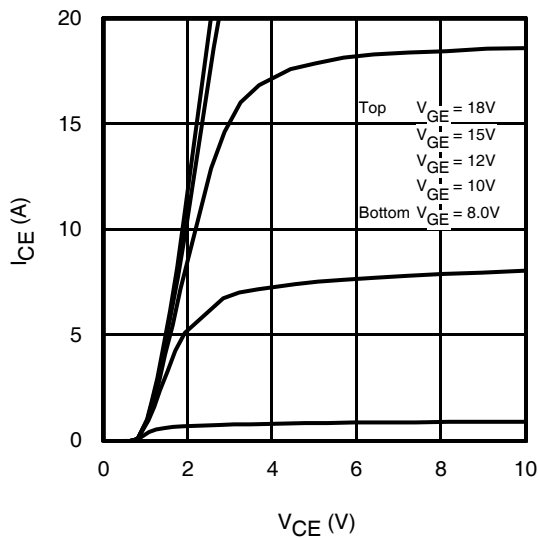
**Fig. 2** - Power Dissipation vs. Case Temperature



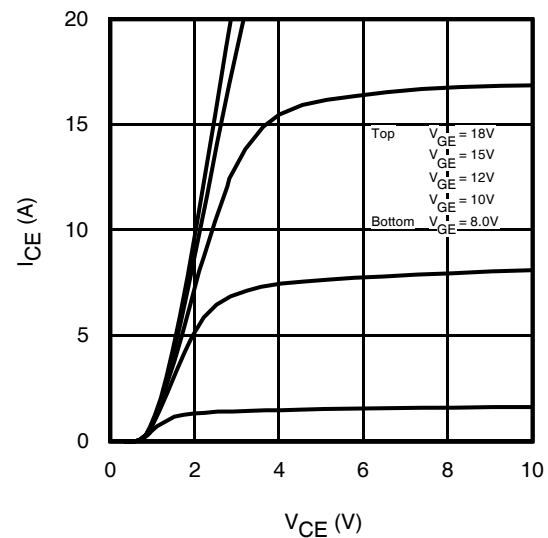
**Fig. 3** - Forward SOA,  
 $T_C = 25^\circ\text{C}$ ,  $T_J \leq 175^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$



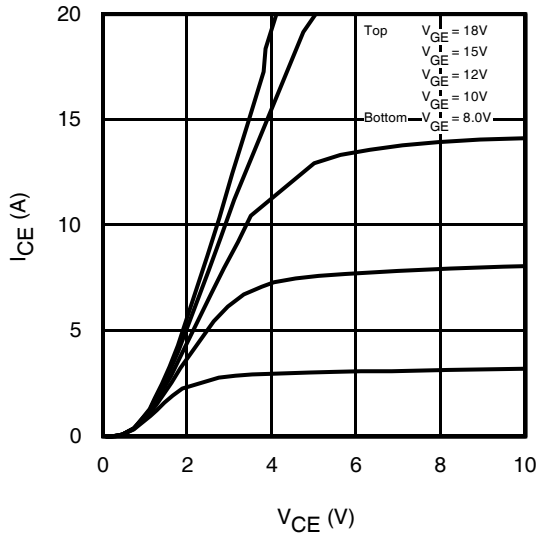
**Fig. 4** - Reverse Bias SOA  
 $T_J = 175^\circ\text{C}$ ,  $V_{GE} = 20\text{V}$



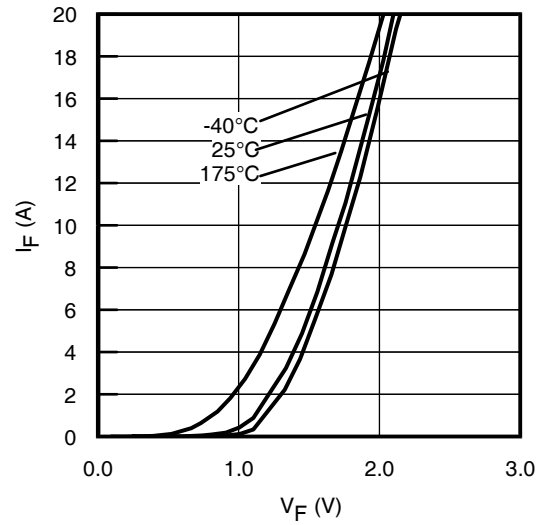
**Fig. 5** - Typ. IGBT Output Characteristics  
 $T_J = -40^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



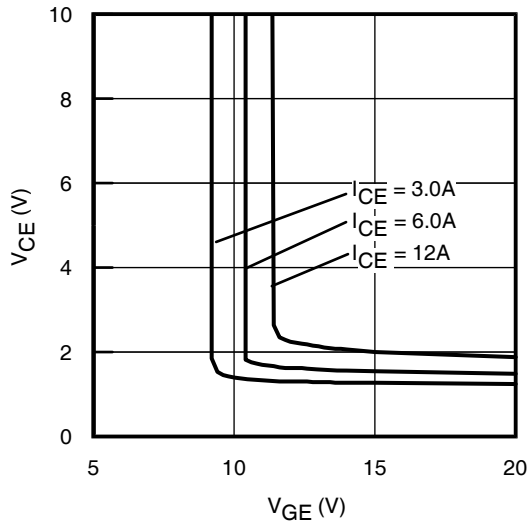
**Fig. 6** - Typ. IGBT Output Characteristics  
 $T_J = 25^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



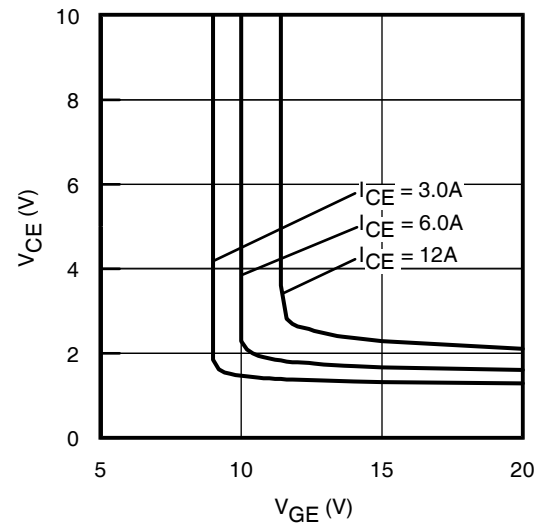
**Fig. 7** - Typ. IGBT Output Characteristics  
 $T_J = 175^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



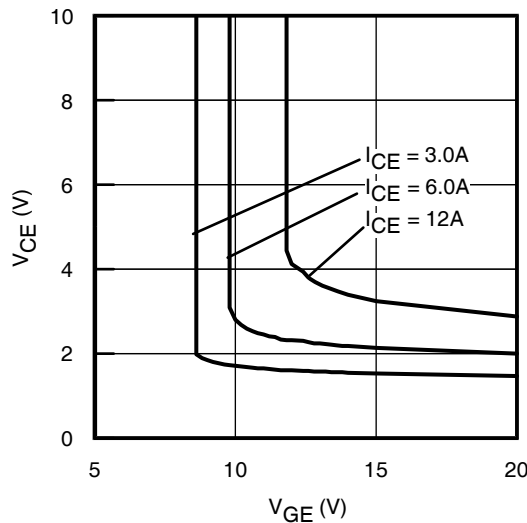
**Fig. 8** - Typ. Diode Forward Characteristics  
 $t_p = 80\mu\text{s}$



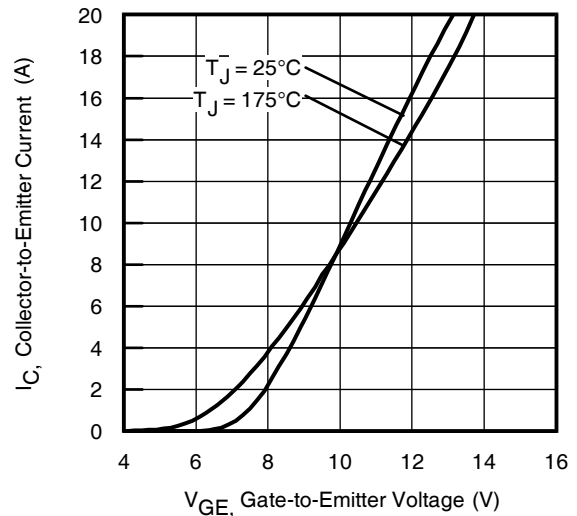
**Fig. 9** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = -40^\circ\text{C}$



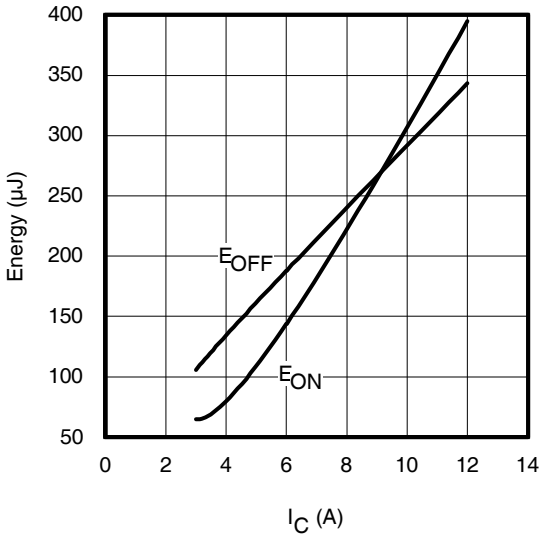
**Fig. 10** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 25^\circ\text{C}$



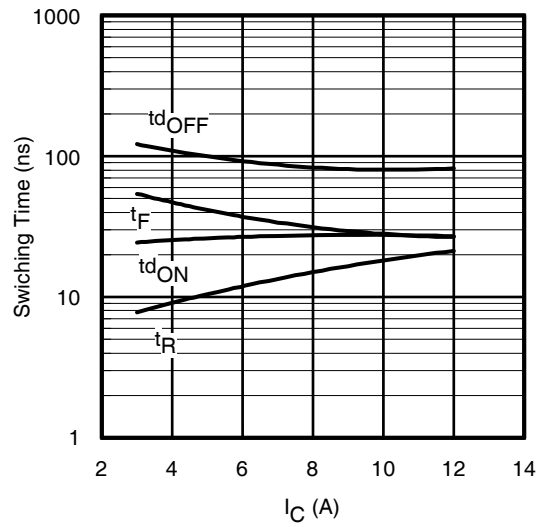
**Fig. 11** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 175^\circ\text{C}$



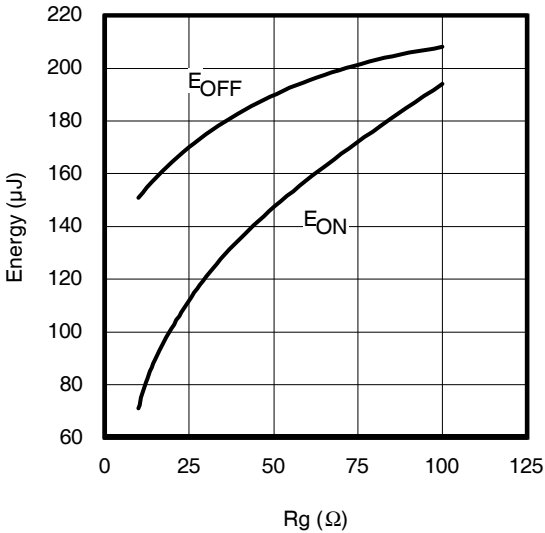
**Fig. 12** - Typ. Transfer Characteristics  
 $V_{CE} = 50\text{V}$ ;  $t_p = 10\mu\text{s}$



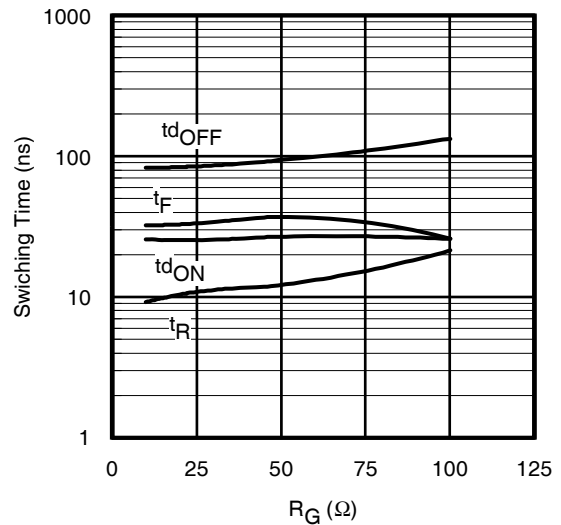
**Fig. 13 - Typ. Energy Loss vs.  $I_C$**   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$ ;  $R_G = 47\Omega$ ;  $V_{GE} = 15\text{V}$ .



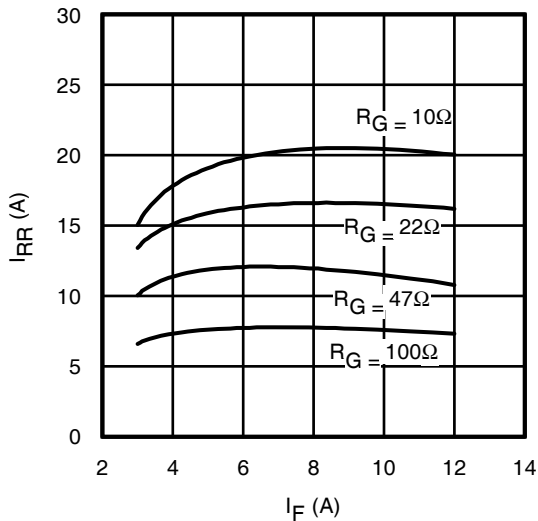
**Fig. 14 - Typ. Switching Time vs.  $I_C$**   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$   
 $R_G = 47\Omega$ ;  $V_{GE} = 15\text{V}$



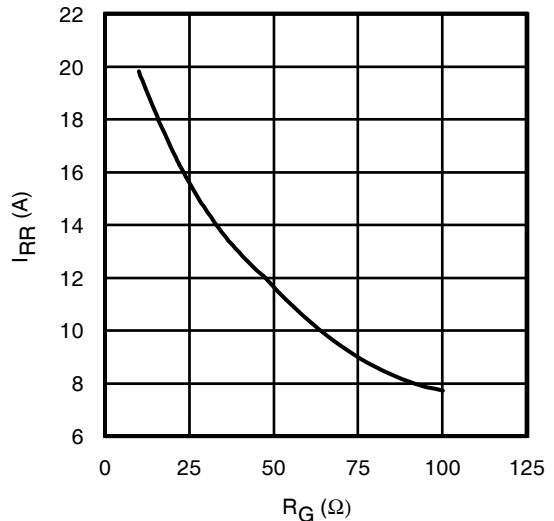
**Fig. 15 - Typ. Energy Loss vs.  $R_G$**   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$ ;  $I_{CE} = 6.0\text{A}$ ;  $V_{GE} = 15\text{V}$



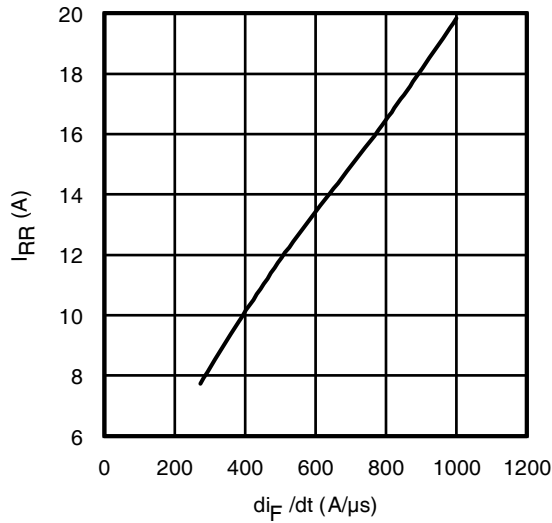
**Fig. 16 - Typ. Switching Time vs.  $R_G$**   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$   
 $I_{CE} = 6.0\text{A}$ ;  $V_{GE} = 15\text{V}$



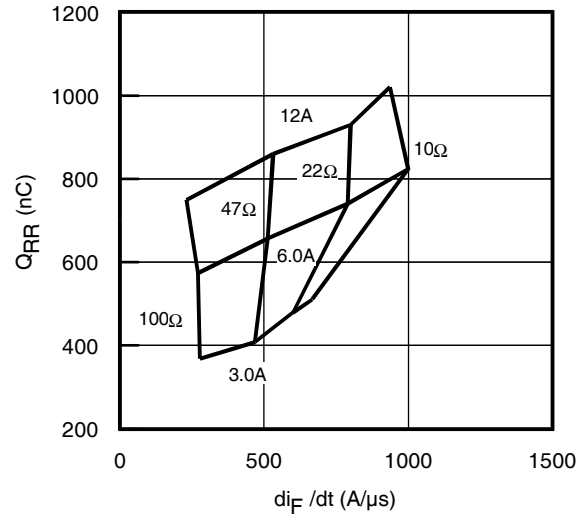
**Fig. 17 - Typical Diode  $I_{RR}$  vs.  $I_F$**   
 $T_J = 175^\circ\text{C}$



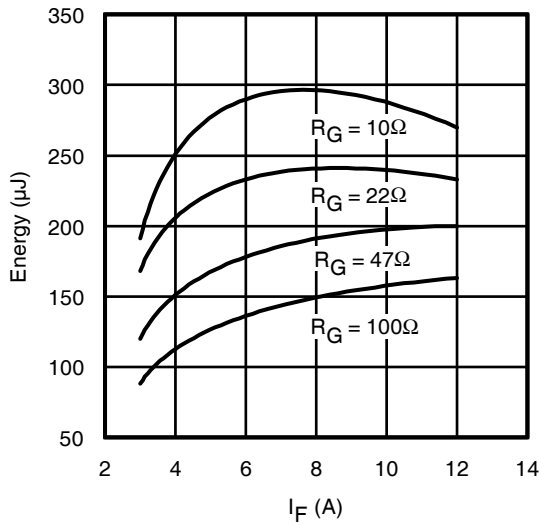
**Fig. 18 - Typical Diode  $I_{RR}$  vs.  $R_G$**   
 $T_J = 175^\circ\text{C}$ ;  $I_F = 6.0\text{A}$



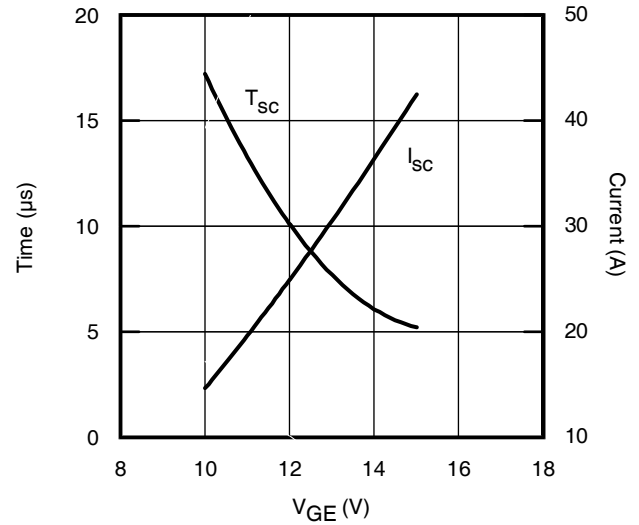
**Fig. 19**- Typical Diode  $I_{RR}$  vs.  $di_F/dt$   
 $V_{CC}=400V$ ;  $V_{GE}=15V$ ;  
 $I_{CE}=6.0A$ ;  $T_J=175^{\circ}C$



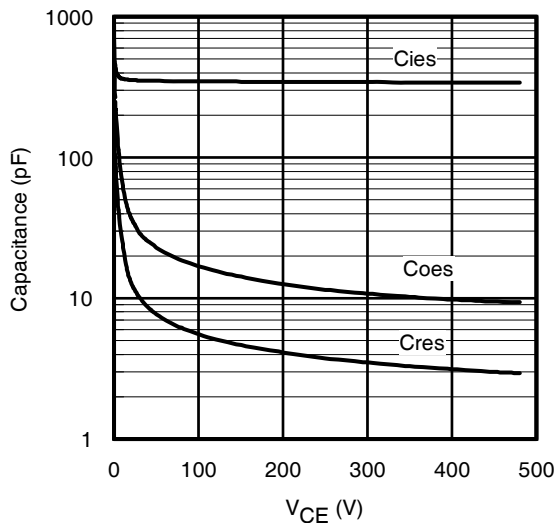
**Fig. 20** - Typical Diode  $Q_{RR}$   
 $V_{CC}=400V$ ;  $V_{GE}=15V$ ;  $T_J=175^{\circ}C$



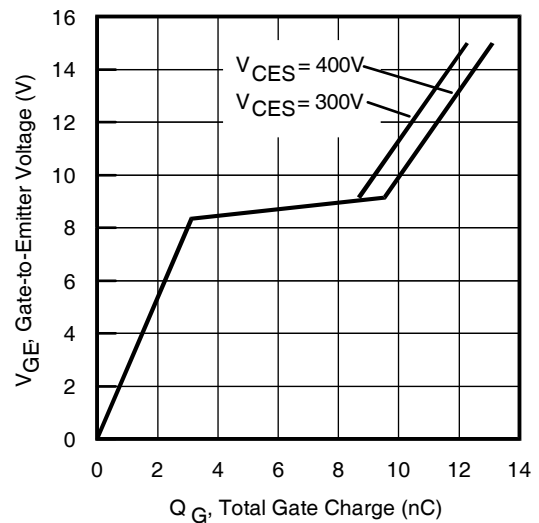
**Fig. 21** - Typical Diode  $E_{RR}$  vs.  $I_F$   
 $T_J=175^{\circ}C$



**Fig. 22**- Typ.  $V_{GE}$  vs. Short Circuit Time  
 $V_{CC}=400V$ ,  $T_C=25^{\circ}C$



**Fig. 23**- Typ. Capacitance vs.  $V_{CE}$   
 $V_{GE}=0V$ ;  $f=1MHz$



**Fig. 24** - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE}=6.0A$ ,  $L=600\mu H$

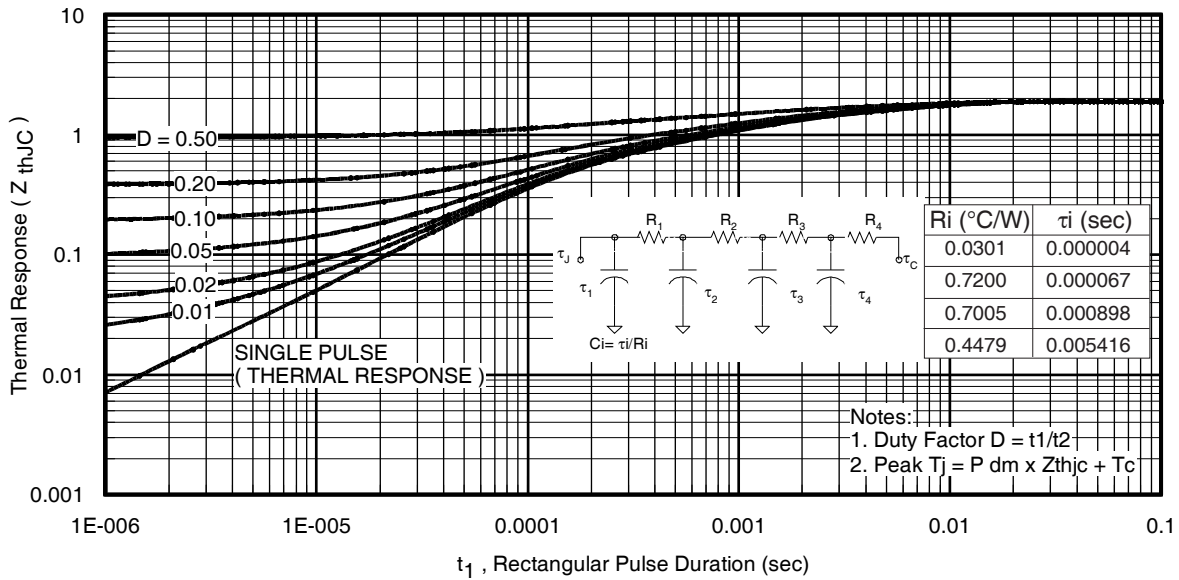


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

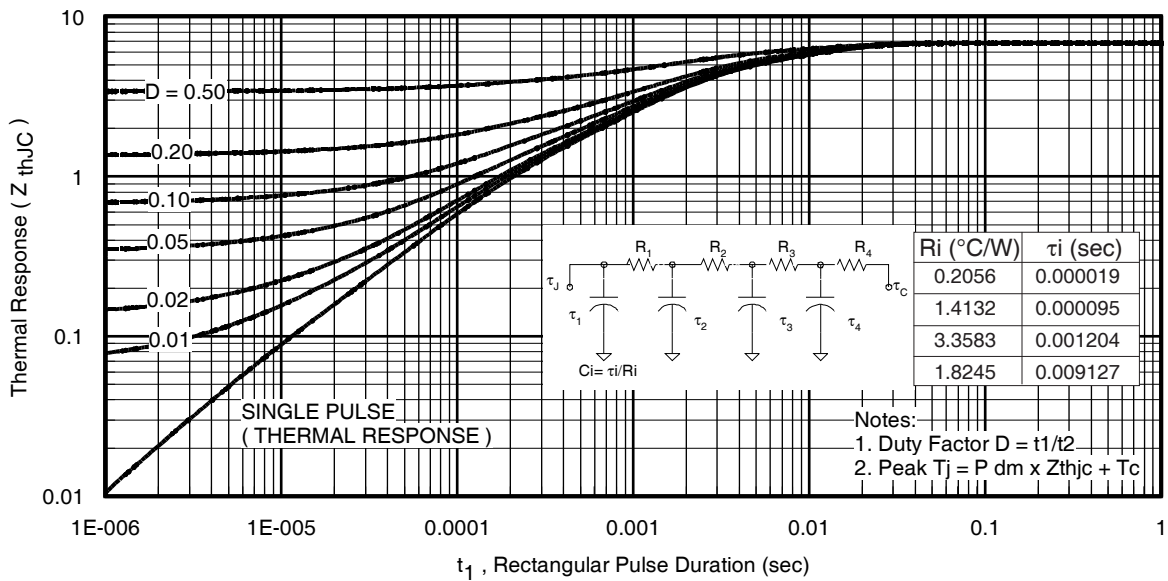
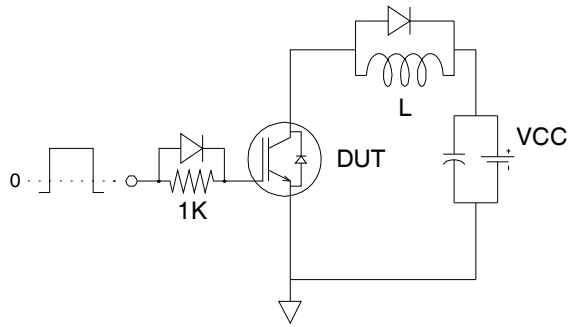
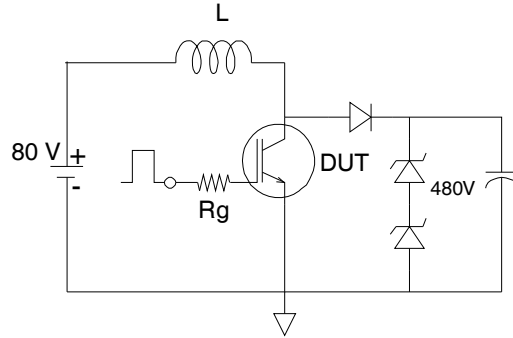


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)



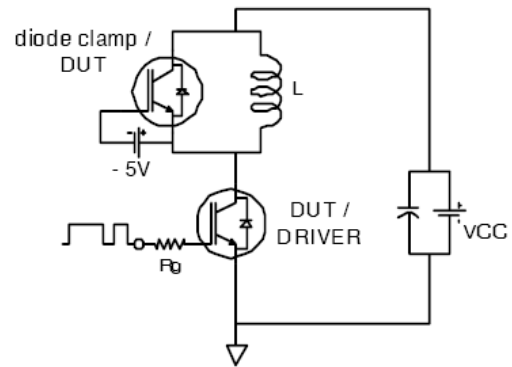
**Fig.C.T.1** - Gate Charge Circuit (turn-off)



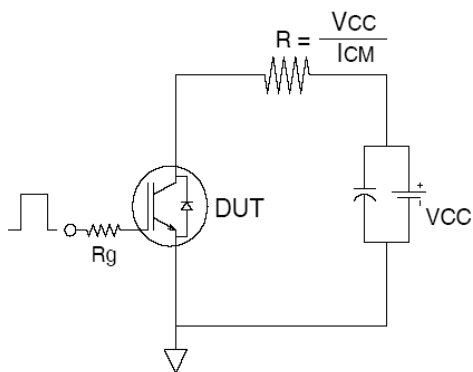
**Fig.C.T.2** - RBSOA Circuit



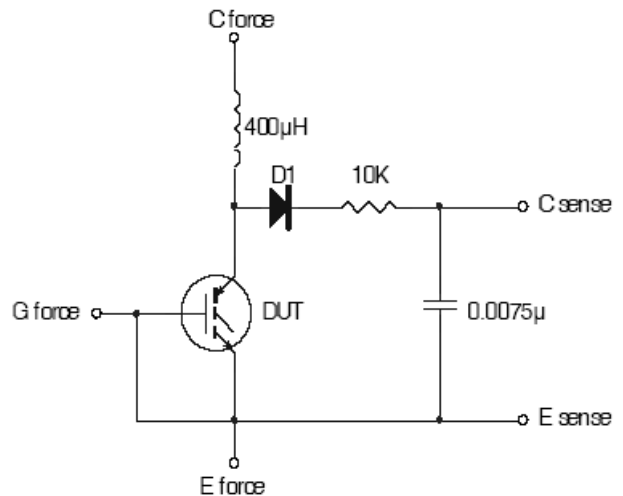
**Fig.C.T.3** - S.C.SOA Circuit



**Fig.C.T.4** - Switching Loss Circuit

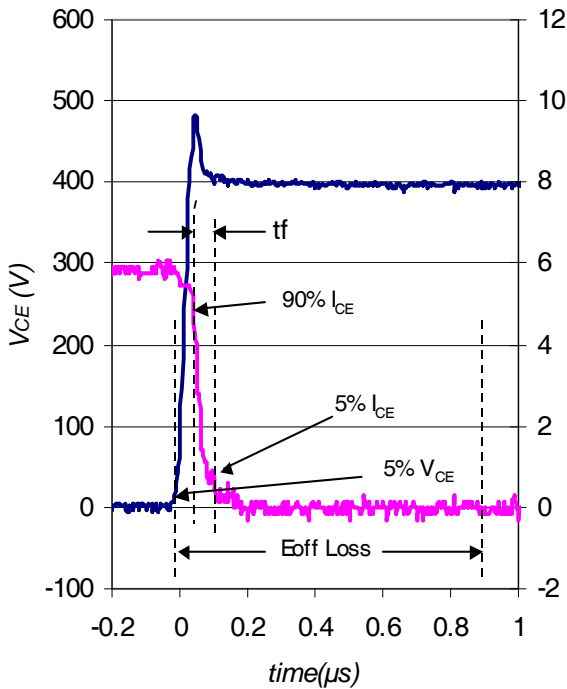


**Fig.C.T.5** - Resistive Load Circuit

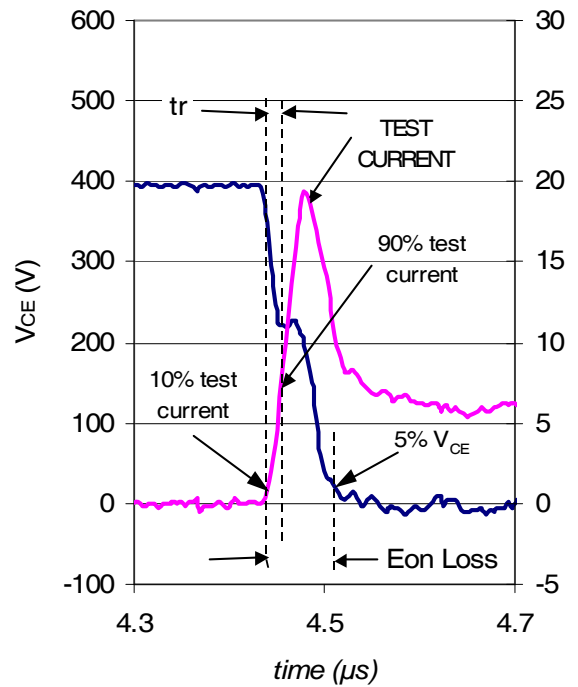


**Fig.C.T.6** - Typical Filter Circuit for  $V_{(BR)CES}$  Measurement

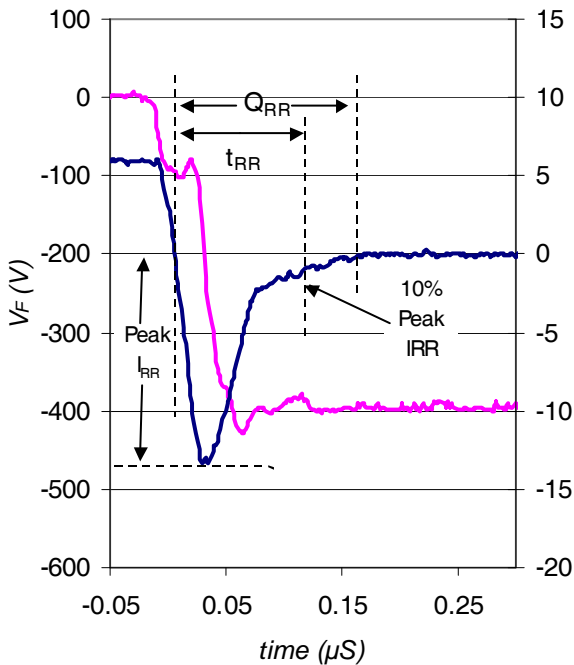




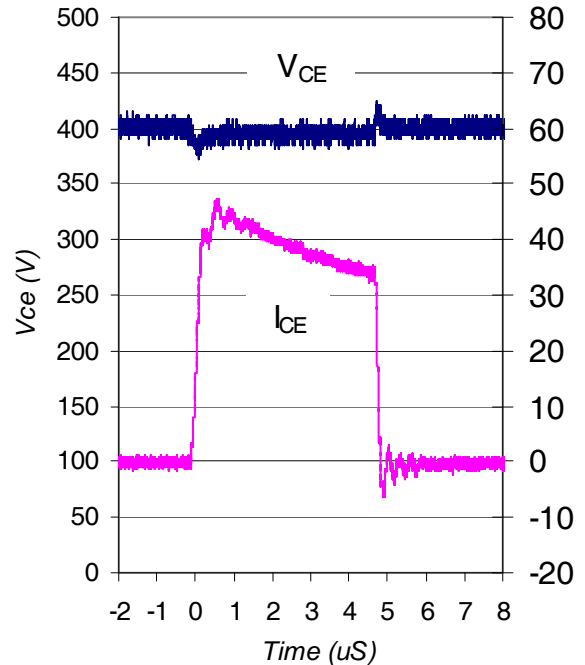
**Fig. WF1** - Typ. Turn-off Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



**Fig. WF2** - Typ. Turn-on Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



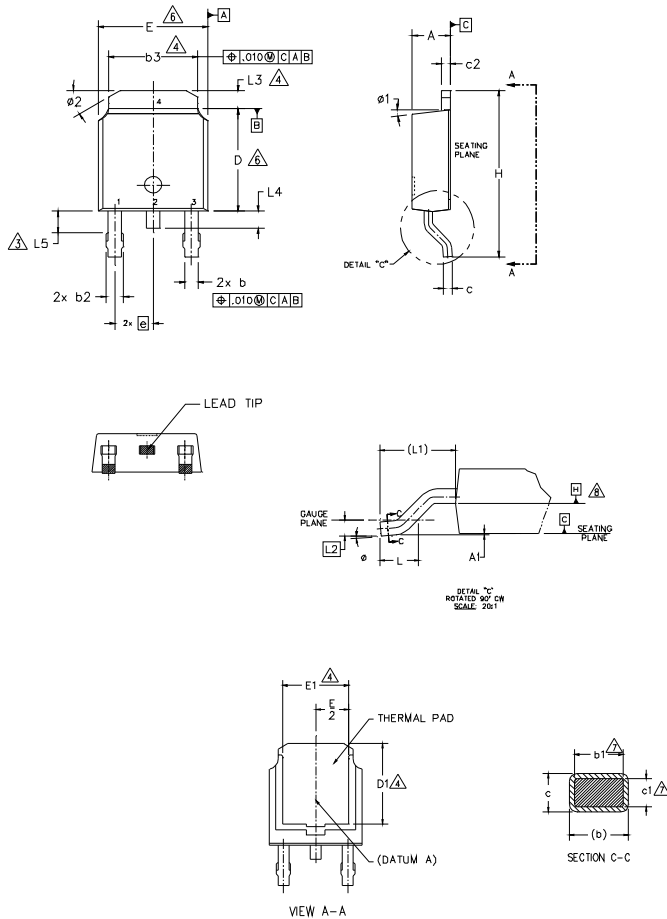
**WF.3**- Typ. Diode Recovery Waveform  
@  $T_J = 175^\circ\text{C}$  using CT.4



**WF.4**- Typ. Short Circuit Waveform  
@  $T_J = 25^\circ\text{C}$  using CT.3

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
- △- LEAD DIMENSION UNCONTROLLED IN L5.
- △- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- △- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- △- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- △- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
φ	0"	10"	0"	10"	
φ1	0"	15"	0"	15"	
φ2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

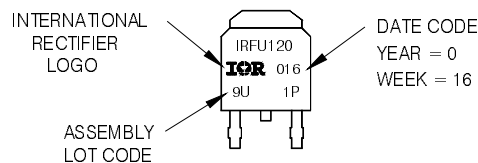
IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

## D-Pak (TO-252AA) Part Marking Information

Notes: This part marking information applies to devices produced before 02/26/2001

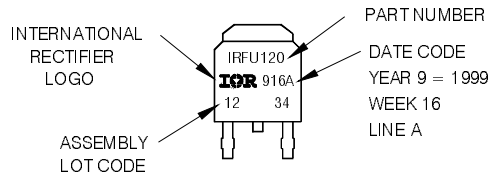
EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 9U1P



DATE CODE  
YEAR = 0  
WEEK = 16

Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE 'A'

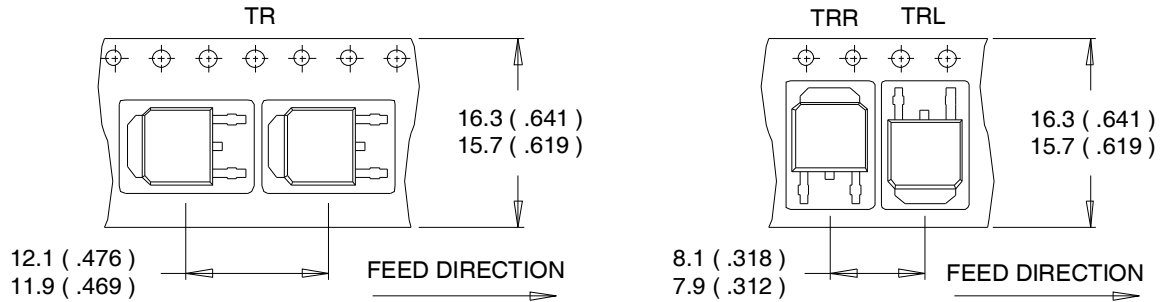


PART NUMBER  
DATE CODE  
YEAR 9 = 1999  
WEEK 16  
LINE A

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

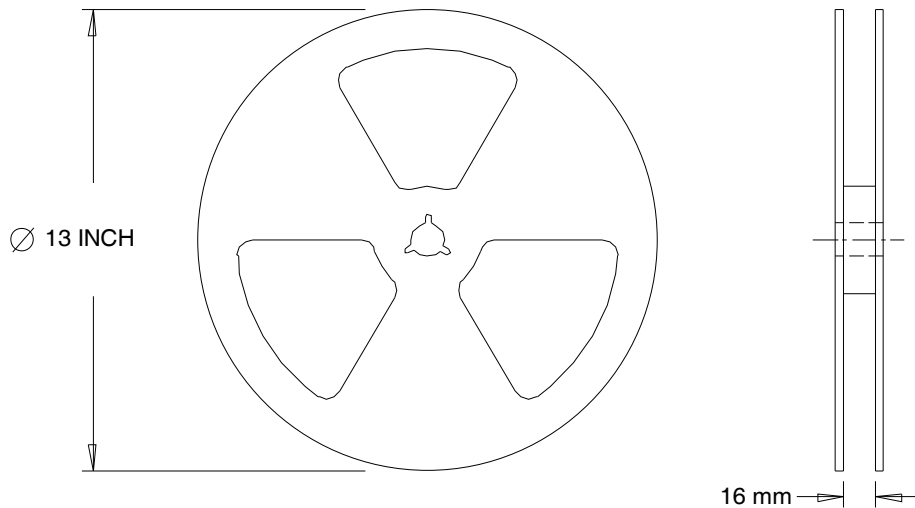
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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Visit us at [www.irf.com](http://www.irf.com) for sales contact information. 10/2012

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)